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Kind regards,

Team Nexperia

74LVC1G3157-Q100

2-channel analog multiplexer/demultiplexer

Rev. 4 — 7 December 2016

Product data sheet

1. General description

The 74LVC1G3157-Q100 provides one analog multiplexer/demultiplexer with one digital select input (S), two independent inputs/outputs (Y0, Y1) and a common input/output (Z).

Schmitt trigger action at the select input makes the circuit tolerant of slower input rise and fall times across the entire V_{CC} range from 1.65 V to 5.5 V.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$
- Wide supply voltage range from 1.65 V to 5.5 V
- Very low ON resistance:
 - ◆ $7.5\text{ }\Omega$ (typical) at $V_{CC} = 2.7\text{ V}$
 - ◆ $6.5\text{ }\Omega$ (typical) at $V_{CC} = 3.3\text{ V}$
 - ◆ $6\text{ }\Omega$ (typical) at $V_{CC} = 5\text{ V}$
- Switch current capability of 32 mA
- Break-before-make switching
- High noise immunity
- CMOS low power consumption
- TTL interface compatibility at 3.3 V
- Latch-up performance meets requirements of JESD 78 Class I
- Control input accepts voltages up to 5.5 V
- Multiple package options
- ESD protection:
 - ◆ MIL-STD-883, method 3015 exceeds 2000 V
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V ($C = 200\text{ pF}$, $R = 0\text{ }\Omega$)



3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74LVC1G3157GW-Q100	−40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363
74LVC1G3157GV-Q100	−40 °C to +125 °C	SC-74	plastic surface-mounted package (TSOP6); 6 leads	SOT457

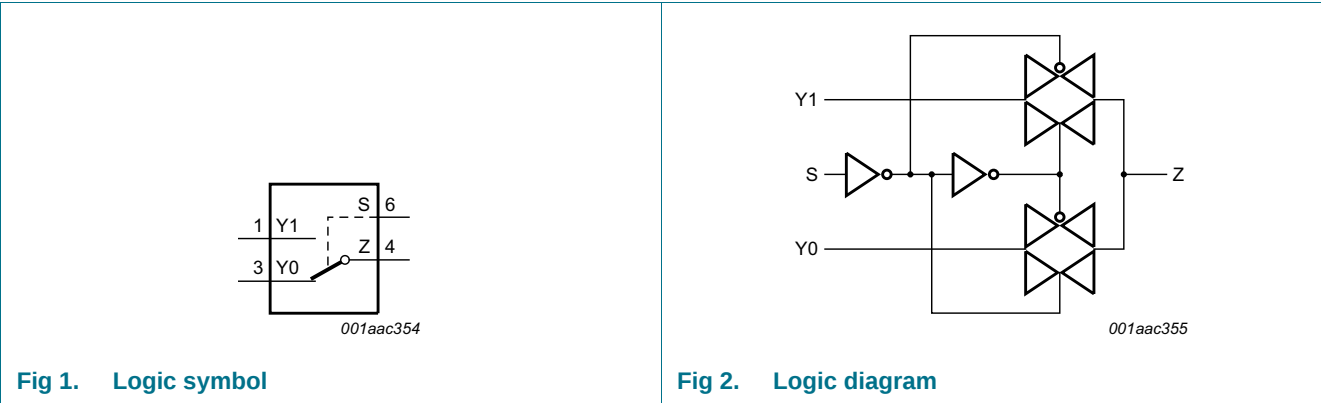
4. Marking

Table 2. Marking

Type number	Marking code ^[1]
74LVC1G3157GW-Q100	YJ
74LVC1G3157GV-Q100	YJ

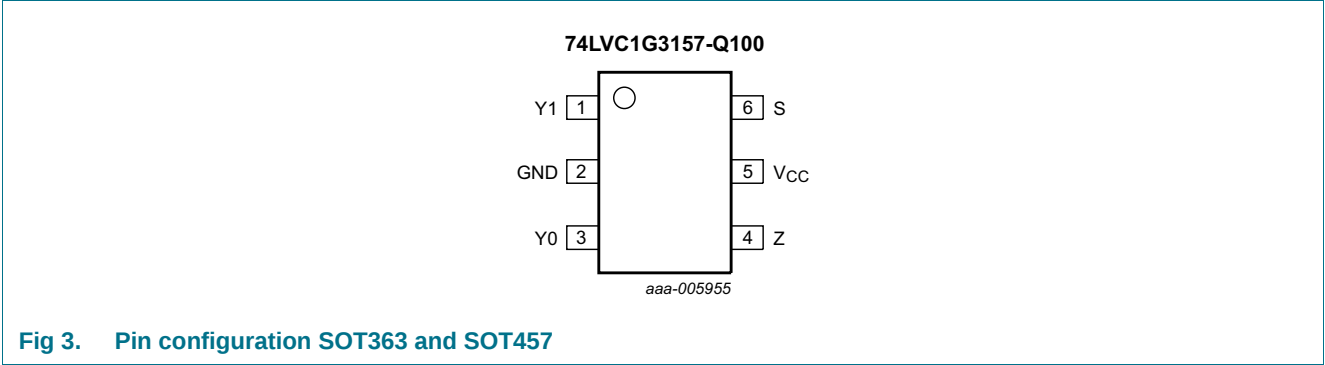
[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
Y1	1	independent input or output
GND	2	ground (0 V)
Y0	3	independent input or output
Z	4	common output or input
V _{CC}	5	supply voltage
S	6	select input

7. Functional description

Table 4. Function table^[1]

Input S	Channel on
L	Y0
H	Y1

[1] H = HIGH voltage level; L = LOW voltage level.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+6.5	V
V_I	input voltage	[1]	-0.5	+6.5	V
I_{IK}	input clamping current	$V_I < -0.5\text{ V}$ or $V_I > V_{CC} + 0.5\text{ V}$	-50	-	mA
I_{SK}	switch clamping current	$V_I < -0.5\text{ V}$ or $V_I > V_{CC} + 0.5\text{ V}$	-	± 50	mA
V_{SW}	switch voltage	enable and disable mode [2]	-0.5	$V_{CC} + 0.5$	V
I_{SW}	switch current	$V_{SW} > -0.5\text{ V}$ or $V_{SW} < V_{CC} + 0.5\text{ V}$	-	± 50	mA
I_{CC}	supply current		-	100	mA
I_{GND}	ground current		-100	-	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40\text{ °C}$ to $+125\text{ °C}$ [3]	-	250	mW

[1] The minimum input voltage rating may be exceeded if the input current rating is observed.

[2] The minimum and maximum switch voltage ratings may be exceeded if the switch clamping current rating is observed.

[3] For SC-88 and SC-74 packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CC}	supply voltage		1.65	-	5.5	V
V_I	input voltage		0	-	5.5	V
V_{SW}	switch voltage	enable and disable mode [1]	0	-	V_{CC}	V
T_{amb}	ambient temperature		-40	-	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 1.65\text{ V}$ to 2.7 V [2]	-	-	20	ns/V
		$V_{CC} = 2.7\text{ V}$ to 5.5 V [2]	-	-	10	ns/V

[1] To avoid sinking GND current from terminal Z when switch current flows in terminal Yn, the voltage drop across the bidirectional switch must not exceed 0.4 V. If the switch current flows into terminal Z, no GND current flows from terminal Yn. In this case, there is no limit for the voltage drop across the switch.

[2] Applies to control signal levels.

10. Static characteristics

Table 7. Static characteristics

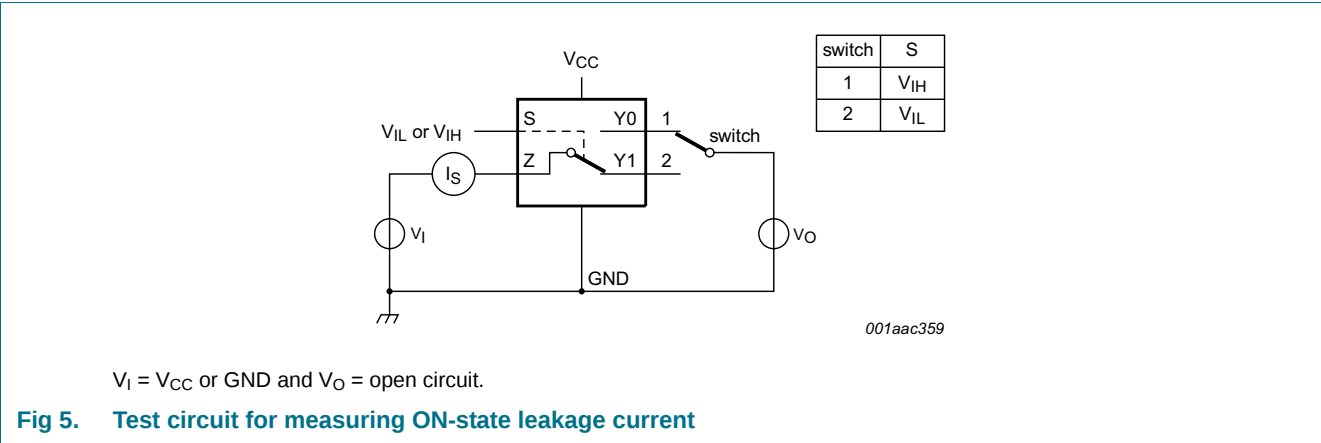
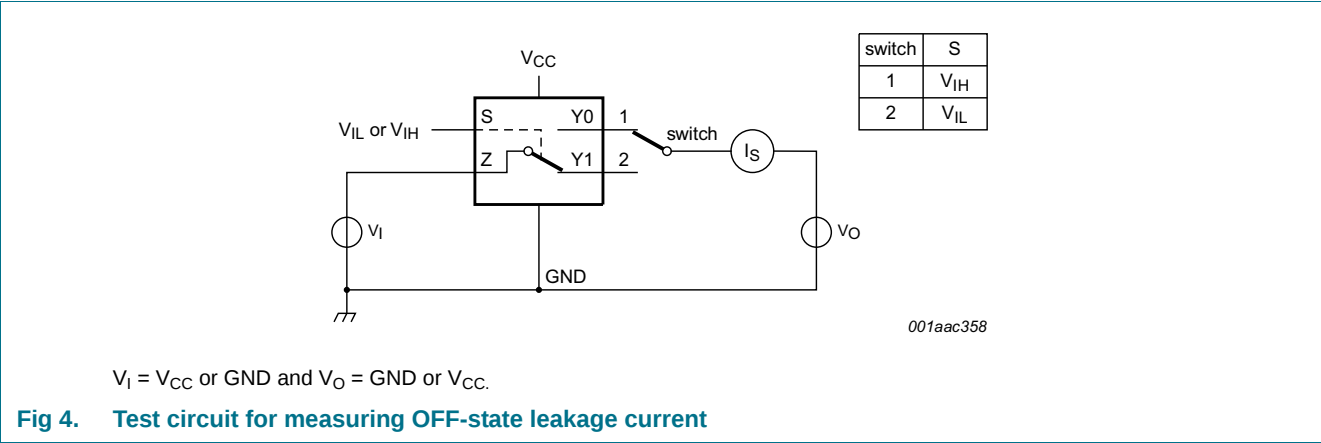
At recommended operating conditions; voltages are referenced to GND (ground 0 V).

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
V _{IH}	HIGH-level input voltage	V _{CC} = 1.65 V to 1.95 V	0.65V _{CC}	-	-	0.65V _{CC}	-	V
		V _{CC} = 2.3 V to 2.7 V	1.7	-	-	1.7	-	V
		V _{CC} = 3 V to 3.6 V	2.0	-	-	2.0	-	V
		V _{CC} = 4.5 V to 5.5 V	0.7V _{CC}	-	-	0.7V _{CC}	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 1.65 V to 1.95 V	-	-	0.35V _{CC}	-	0.35V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	-	0.7	V
		V _{CC} = 3 V to 3.6 V	-	-	0.8	-	0.8	V
		V _{CC} = 4.5 V to 5.5 V	-	-	0.3V _{CC}	-	0.3V _{CC}	V
I _I	input leakage current	pin S; V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V ^[2]	-	±0.1	±1	-	±1	μA
I _{S(OFF)}	OFF-state leakage current	V _{CC} = 5.5 V; see Figure 4 ^[2]	-	±0.1	±0.2	-	±0.5	μA
I _{S(ON)}	ON-state leakage current	V _{CC} = 5.5 V; see Figure 5 ^[2]	-	±0.1	±1	-	±2	μA
I _{CC}	supply current	V _I = 5.5 V or GND; V _{SW} = GND or V _{CC} ; V _{CC} = 1.65 V to 5.5 V ^[2]	-	0.1	4	-	4	μA
ΔI _{CC}	additional supply current	pin S; V _I = V _{CC} – 0.6 V; V _{CC} = 5.5 V; V _{SW} = GND or V _{CC} ^[2]	-	5	500	-	500	μA
C _I	input capacitance		-	2.5	-	-	-	pF
C _{S(OFF)}	OFF-state capacitance		-	6.0	-	-	-	pF
C _{S(ON)}	ON-state capacitance		-	18	-	-	-	pF

[1] Typical values are measured at T_{amb} = 25 °C.

[2] These typical values are measured at V_{CC} = 3.3 V

10.1 Test circuits



10.2 ON resistance

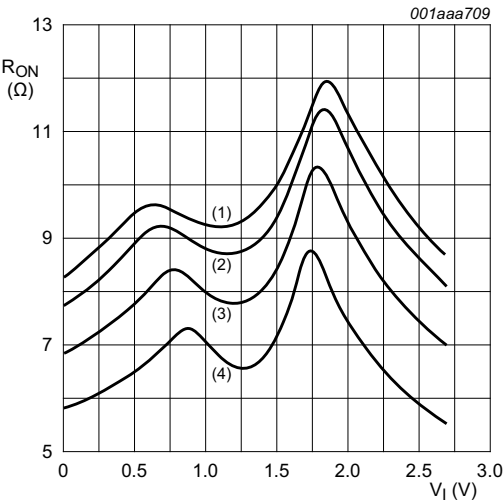
Table 8. ON resistance

At recommended operating conditions; voltages are referenced to GND (ground 0 V); for graphs see [Figure 7](#) to [Figure 12](#).

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
R _{ON(peak)}	ON resistance (peak)	V _I = GND to V _{CC} ; see Figure 6						
		I _{SW} = 4 mA; V _{CC} = 1.65 V to 1.95 V	-	34.0	130	-	195	Ω
		I _{SW} = 8 mA; V _{CC} = 2.3 V to 2.7 V	-	12.0	30	-	45	Ω
		I _{SW} = 12 mA; V _{CC} = 2.7 V	-	10.4	25	-	38	Ω
		I _{SW} = 24 mA; V _{CC} = 3 V to 3.6 V	-	7.8	20	-	30	Ω
		I _{SW} = 32 mA; V _{CC} = 4.5 V to 5.5 V	-	6.2	15	-	23	Ω
R _{ON(rail)}	ON resistance (rail)	V _I = GND; see Figure 6						
		I _{SW} = 4 mA; V _{CC} = 1.65 V to 1.95 V	-	8.2	18	-	27	Ω
		I _{SW} = 8 mA; V _{CC} = 2.3 V to 2.7 V	-	7.1	16	-	24	Ω
		I _{SW} = 12 mA; V _{CC} = 2.7 V	-	6.9	14	-	21	Ω
		I _{SW} = 24 mA; V _{CC} = 3 V to 3.6 V	-	6.5	12	-	18	Ω
		I _{SW} = 32 mA; V _{CC} = 4.5 V to 5.5 V	-	5.8	10	-	15	Ω
		V _I = V _{CC} ; see Figure 6						
		I _{SW} = 4 mA; V _{CC} = 1.65 V to 1.95 V	-	10.4	30	-	45	Ω
		I _{SW} = 8 mA; V _{CC} = 2.3 V to 2.7 V	-	7.6	20	-	30	Ω
		I _{SW} = 12 mA; V _{CC} = 2.7 V	-	7.0	18	-	27	Ω
		I _{SW} = 24 mA; V _{CC} = 3 V to 3.6 V	-	6.1	15	-	23	Ω
		I _{SW} = 32 mA; V _{CC} = 4.5 V to 5.5 V	-	4.9	10	-	15	Ω
R _{ON(flat)}	ON resistance (flatness)	V _I = GND to V _{CC} ^[2]						
		I _{SW} = 4 mA; V _{CC} = 1.65 V to 1.95 V	-	26.0	-	-	-	Ω
		I _{SW} = 8 mA; V _{CC} = 2.3 V to 2.7 V	-	5.0	-	-	-	Ω
		I _{SW} = 12 mA; V _{CC} = 2.7 V	-	3.5	-	-	-	Ω
		I _{SW} = 24 mA; V _{CC} = 3 V to 3.6 V	-	2.0	-	-	-	Ω
		I _{SW} = 32 mA; V _{CC} = 4.5 V to 5.5 V	-	1.5	-	-	-	Ω

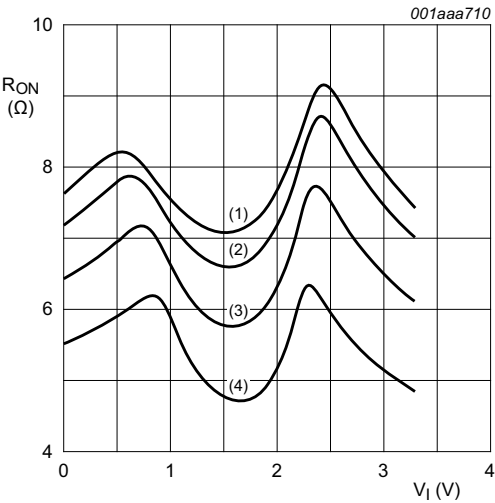
[1] Typical values are measured at T_{amb} = 25 °C and nominal V_{CC}.

[2] Flatness is defined as the difference between the maximum and minimum value of ON resistance measured at identical V_{CC} and temperature.



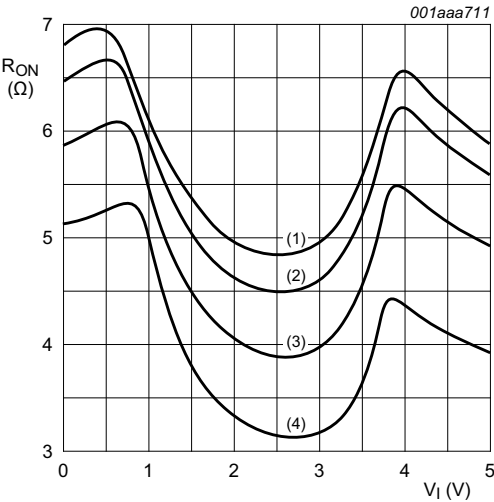
- (1) $T_{amb} = 125$ $^{\circ}\text{C}$.
- (2) $T_{amb} = 85$ $^{\circ}\text{C}$.
- (3) $T_{amb} = 25$ $^{\circ}\text{C}$.
- (4) $T_{amb} = -40$ $^{\circ}\text{C}$.

Fig 10. ON resistance as a function of input voltage; $V_{CC} = 2.7$ V



- (1) $T_{amb} = 125$ $^{\circ}\text{C}$.
- (2) $T_{amb} = 85$ $^{\circ}\text{C}$.
- (3) $T_{amb} = 25$ $^{\circ}\text{C}$.
- (4) $T_{amb} = -40$ $^{\circ}\text{C}$.

Fig 11. ON resistance as a function of input voltage; $V_{CC} = 3.3$ V



- (1) $T_{amb} = 125$ $^{\circ}\text{C}$.
- (2) $T_{amb} = 85$ $^{\circ}\text{C}$.
- (3) $T_{amb} = 25$ $^{\circ}\text{C}$.
- (4) $T_{amb} = -40$ $^{\circ}\text{C}$.

Fig 12. ON resistance as a function of input voltage; $V_{CC} = 5.0$ V

11. Dynamic characteristics

Table 9. Dynamic characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); for load circuit see [Figure 16](#).

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
t _{pd}	propagation delay	Z to Yn or Yn to Z; see Figure 13 ^{[2][3]}						
		V _{CC} = 1.65 V to 1.95 V	-	-	2	-	3.0	ns
		V _{CC} = 2.3 V to 2.7 V	-	-	1.2	-	2.0	ns
		V _{CC} = 2.7 V	-	-	1.0	-	1.5	ns
		V _{CC} = 3 V to 3.6 V	-	-	0.8	-	1.5	ns
		V _{CC} = 4.5 V to 5.5 V	-	-	0.6	-	1.0	ns
t _{en}	enable time	S to Yn; see Figure 14 ^[4]						
		V _{CC} = 1.65 V to 1.95 V	3.1	8.7	20.8	3.1	22.0	ns
		V _{CC} = 2.3 V to 2.7 V	2.2	5.3	11.5	2.2	12.5	ns
		V _{CC} = 2.7 V	2.1	4.9	9.3	2.1	10.2	ns
		V _{CC} = 3 V to 3.6 V	1.8	4.0	7.6	1.8	9.0	ns
		V _{CC} = 4.5 V to 5.5 V	1.5	3.0	5.7	1.5	6.1	ns
t _{dis}	disable time	S to Yn; see Figure 14 ^[5]						
		V _{CC} = 1.65 V to 1.95 V	3.0	6.0	11.4	3.0	11.7	ns
		V _{CC} = 2.3 V to 2.7 V	2.1	4.4	7.3	2.1	7.6	ns
		V _{CC} = 2.7 V	2.1	4.2	6.3	2.1	6.6	ns
		V _{CC} = 3 V to 3.6 V	1.7	3.6	5.3	1.7	5.9	ns
		V _{CC} = 4.5 V to 5.5 V	1.3	2.9	3.8	1.3	4.3	ns
t _{b-m}	break-before-make time	see Figure 15 ^[6]						
		V _{CC} = 1.65 V to 1.95 V	0.5	-	-	0.5	-	ns
		V _{CC} = 2.3 V to 2.7 V	0.5	-	-	0.5	-	ns
		V _{CC} = 2.7 V	0.5	-	-	0.5	-	ns
		V _{CC} = 3 V to 3.6 V	0.5	-	-	0.5	-	ns
		V _{CC} = 4.5 V to 5.5 V	0.5	-	-	0.5	-	ns

[1] Typical values are measured at T_{amb} = 25 °C and nominal V_{CC}.

[2] t_{pd} is the same as t_{PLH} and t_{PHL}.

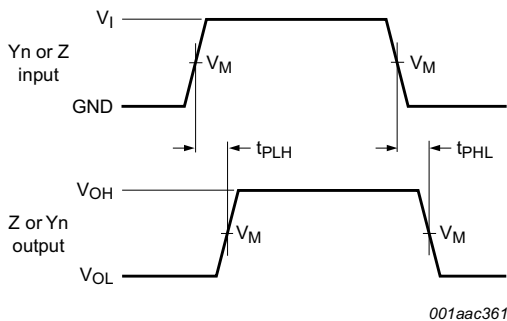
[3] Propagation delay is the calculated RC time constant of the typical ON resistance of the switch and the specified capacitance when driven by an ideal voltage source (zero output impedance).

[4] t_{en} is the same as t_{PZH} and t_{PZL}.

[5] t_{dis} is the same as t_{PLZ} and t_{PHZ}.

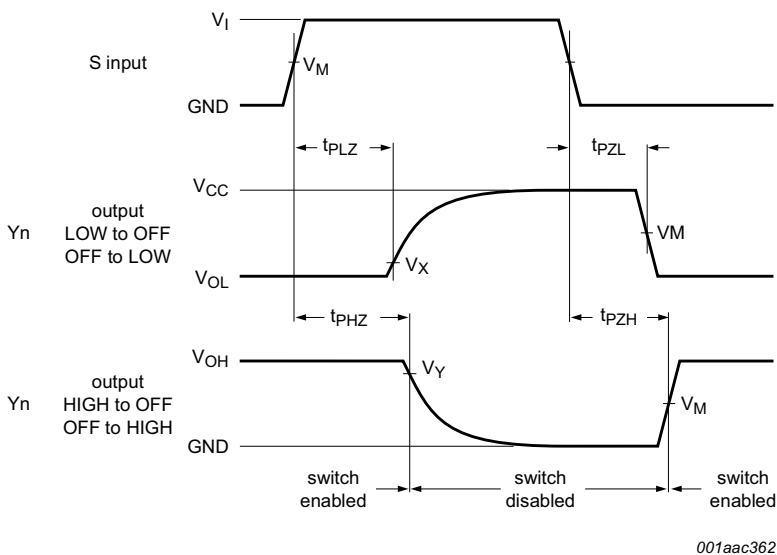
[6] Break-before-make specified by design.

11.1 Waveforms and test circuits



Measurement points are given in [Table 10](#).
Logic levels: VOL and VOH are typical output voltage levels that occur with the output load.

Fig 13. Input (Yn or Z) to output (Z or Yn) propagation delays

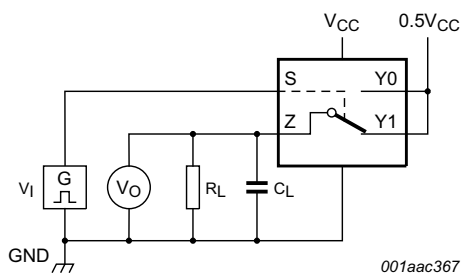


Measurement points are given in [Table 10](#).
Logic levels: VOL and VOH are typical output voltage levels that occur with the output load.

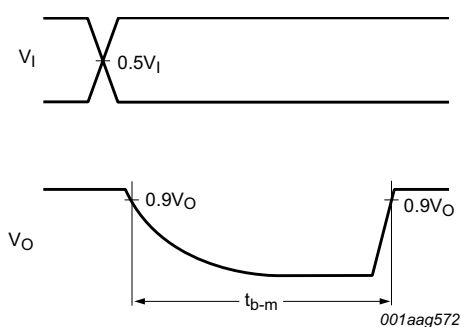
Fig 14. Enable and disable times

Table 10. Measurement points

Supply voltage	Input	Output		
V _{CC}	V _M	V _M	V _X	V _Y
1.65 V to 5.5 V	0.5 × V _{CC}	0.5 × V _{CC}	V _{OL} + 0.3 V	V _{OH} - 0.3 V

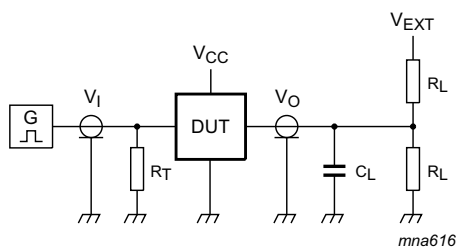


a. Test circuit



b. Input and output measurement points

Fig 15. Test circuit for measuring break-before-make timing



Test data is given in [Table 11](#).

Definitions test circuit:

R_T = Termination resistance should be equal to output impedance Z_0 of the pulse generator.

C_L = Load capacitance including jig and probe capacitance.

R_L = Load resistance.

V_{EXT} = External voltage for measuring switching times.

Fig 16. Test circuit for measuring switching times

Table 11. Test data

Supply voltage	Input		Load		V _{EXT}		
V _{CC}	V _I	t _r , t _f	C _L	R _L	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
1.65 V to 1.95 V	V _{CC}	≤ 2.0 ns	50 pF	500 Ω	open	GND	2 × V _{CC}
2.3 V to 2.7 V	V _{CC}	≤ 2.0 ns	50 pF	500 Ω	open	GND	2 × V _{CC}
2.7 V	V _{CC}	≤ 2.5 ns	50 pF	500 Ω	open	GND	2 × V _{CC}
3 V to 3.6 V	V _{CC}	≤ 2.5 ns	50 pF	500 Ω	open	GND	2 × V _{CC}
4.5 V to 5.5 V	V _{CC}	≤ 2.5 ns	50 pF	500 Ω	open	GND	2 × V _{CC}

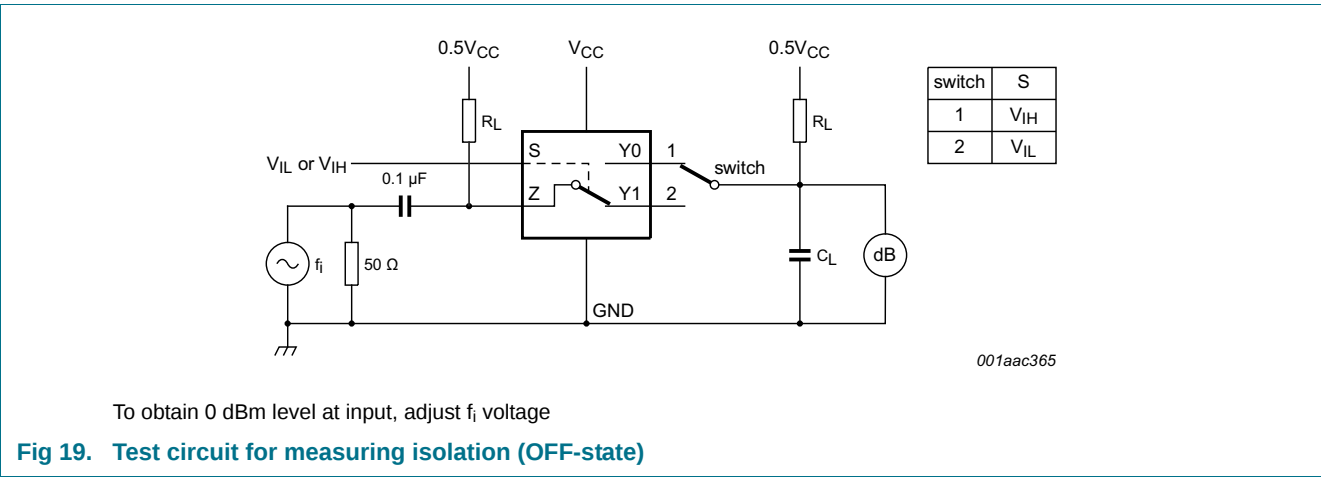
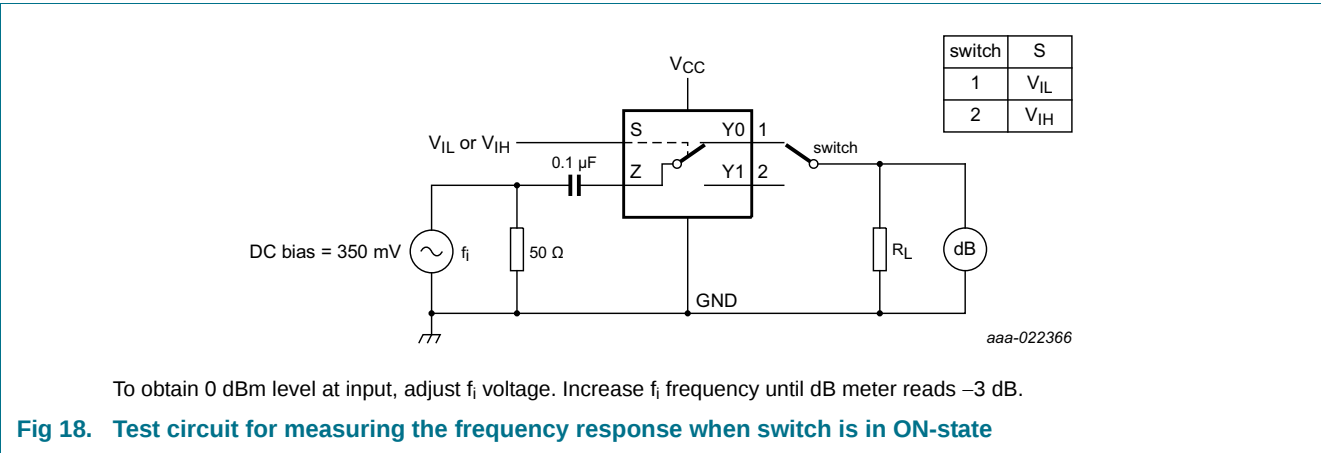
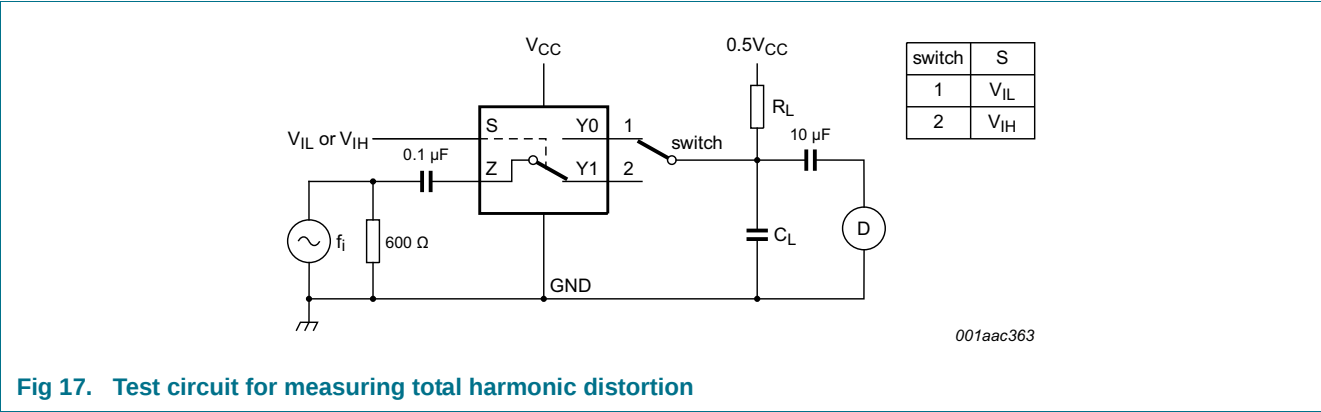
11.2 Additional dynamic characteristics

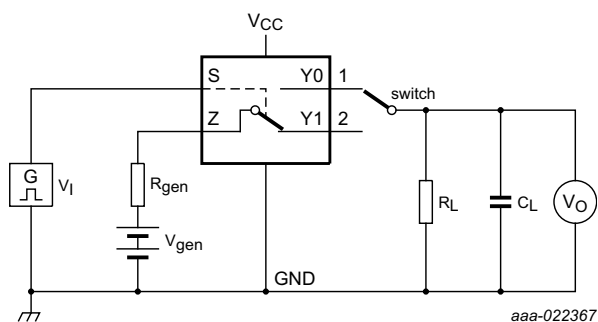
Table 12. Additional dynamic characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); T_{amb} = 25 °C.

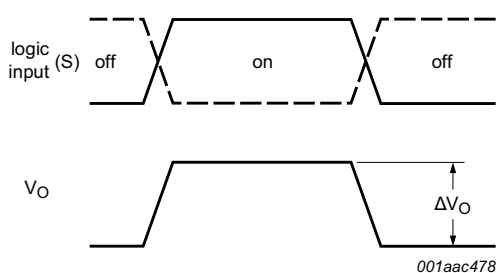
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
THD	total harmonic distortion	f _i = 600 Hz to 20 kHz; R _L = 600 Ω; C _L = 50 pF; V _I = 0.5 V (p-p); see Figure 17				
		V _{CC} = 1.65 V	-	0.260	-	%
		V _{CC} = 2.3 V	-	0.078	-	%
		V _{CC} = 3.0 V	-	0.078	-	%
		V _{CC} = 4.5 V	-	0.078	-	%
f _(-3dB)	-3 dB frequency response	R _L = 50 Ω; see Figure 18				
		V _{CC} = 1.65 V	-	200	-	MHz
		V _{CC} = 2.3 V	-	300	-	MHz
		V _{CC} = 3.0 V	-	300	-	MHz
		V _{CC} = 4.5 V	-	300	-	MHz
α _{iso}	isolation (OFF-state)	R _L = 50 Ω; C _L = 5 pF; f _i = 10 MHz; see Figure 19				
		V _{CC} = 1.65 V	-	-42	-	dB
		V _{CC} = 2.3 V	-	-42	-	dB
		V _{CC} = 3.0 V	-	-40	-	dB
		V _{CC} = 4.5 V	-	-40	-	dB
Q _{inj}	charge injection	C _L = 0.1 nF; V _{gen} = 0 V; R _{gen} = 0 Ω; f _i = 1 MHz; R _L = 1 MΩ; see Figure 20				
		V _{CC} = 1.8 V	-	3.3	-	pC
		V _{CC} = 2.5 V	-	4.1	-	pC
		V _{CC} = 3.3 V	-	5.0	-	pC
		V _{CC} = 4.5 V	-	6.4	-	pC
		V _{CC} = 5.5 V	-	7.5	-	pC

11.3 Test circuits





a. Test circuit



b. Input and output pulse definitions

$$Q_{inj} = \Delta V_O \times C_L$$

ΔV_O = output voltage variation.

R_{gen} = generator resistance.

V_{gen} = generator voltage.

Fig 20. Test circuit for measuring charge injection

12. Package outline

Plastic surface-mounted package; 6 leadsSOT363

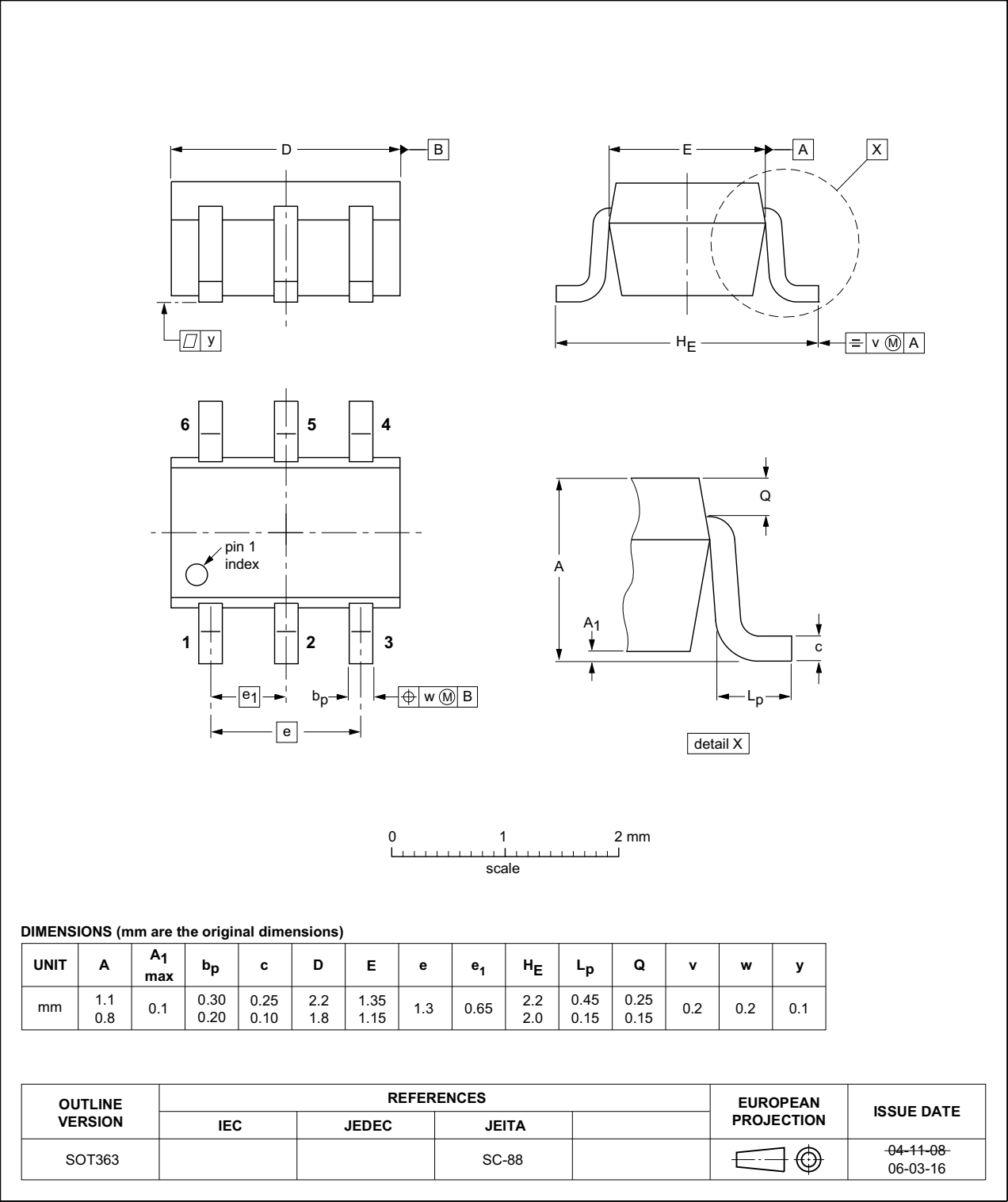


Fig 21. Package outline SOT363 (SC-88)

Plastic surface-mounted package (TSOP6); 6 leads

SOT457

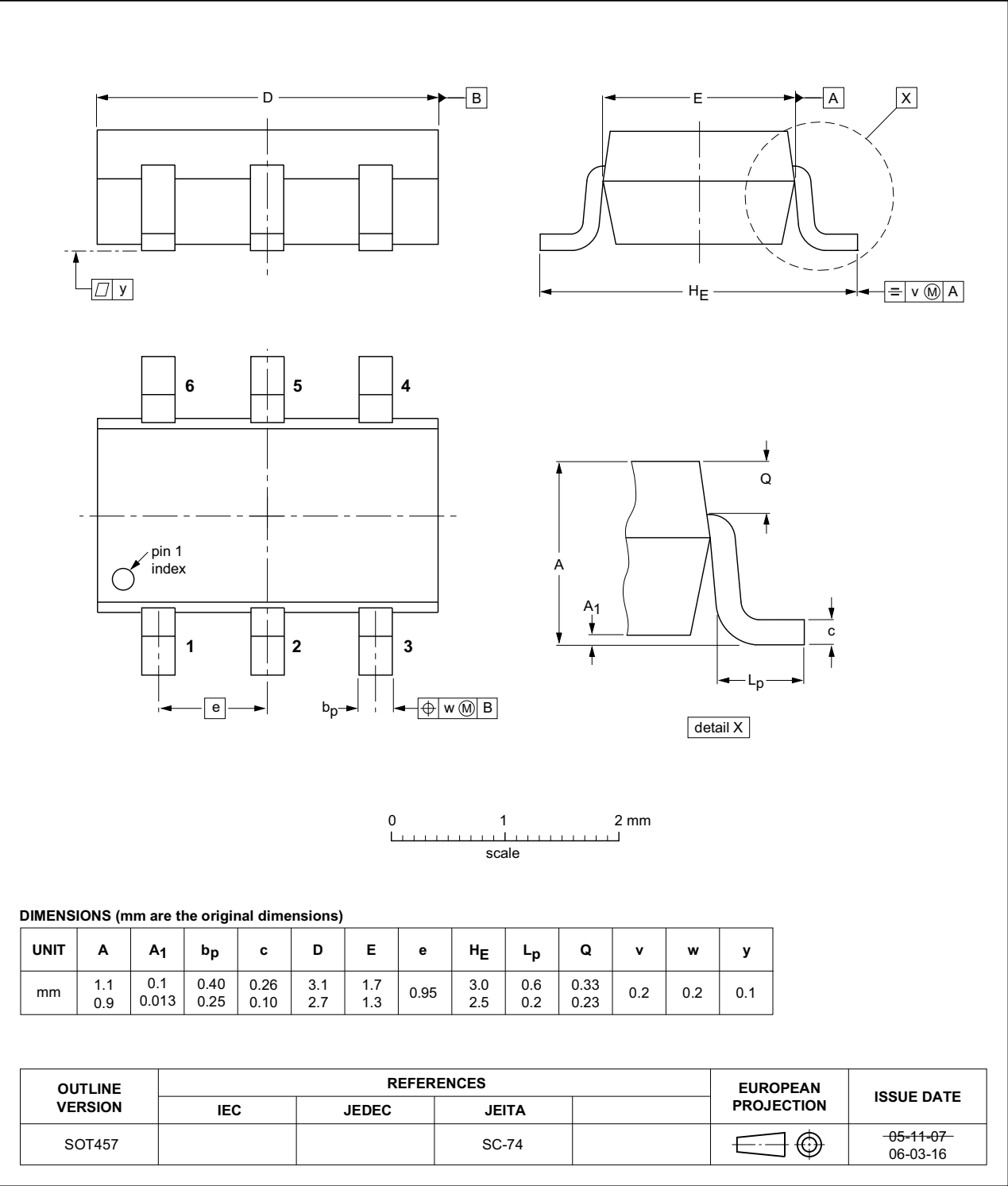


Fig 22. Package outline SOT457 (SC-74)

13. Abbreviations

Table 13. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
TTL	Transistor-Transistor Logic
HBM	Human Body Model
ESD	ElectroStatic Discharge
MM	Machine Model
MIL	Military
DUT	Device Under Test

14. Revision history

Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC1G3157_Q100 v.4	20161207	Product data sheet	-	74LVC1G3157_Q100 v.3
Modifications:	• Table 7: The maximum limits for leakage current and supply current have changed.			
74LVC1G3157_Q100 v.3	20160531	Product data sheet	-	74LVC1G3157_Q100 v.2
Modifications:	• Table 9: Minimum and maximum values enable and disable times revised. • Table 12 and Figure 18: Condition and test circuit for $f_{(-3dB)}$ revised. • Figure 20: Test circuit for charge injection revised.			
74LVC1G3157_Q100 v.2	20130410	Product data sheet	-	74LVC1G3157_Q100 v.1
Modifications:	• Type number 74LVC1G3157GM-Q100 has been removed.			
74LVC1G3157_Q100 v.1	20130219	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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